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# INTEGRATED CIRCUITS, SILICON MONOLITHIC, CMOS DUAL J-K MASTER SLAVE FLIP-FLOP, BASED ON TYPE 4027B

ESCC Detail Specification No. 9203/022

# ISSUE 1 October 2002





#### **ESCC Detail Specification**

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# INTEGRATED CIRCUITS, SILICON MONOLITHIC, CMOS DUAL J-K MASTER SLAVE FLIP-FLOP, BASED ON TYPE 4027B

ESA/SCC Detail Specification No. 9203/022



# space components coordination group

		Approved by		
Issue/Rev.	Date	SCCG Chairman	ESA Director General or his Deputy	
Issue 4	April 2001	Sa Mitt	Am	



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# **DOCUMENTATION CHANGE NOTICE**

		DOCUMENTATION CHANGE NOTICE	
Rev.	Rev.	CHANGE	Approved
Letter	Date	Reference Item	DCR No.
		This Issue supersedes Issue 3 and incorporates all modific Revisions 'A', 'B' and 'C' to Issue 3 and the changes agree DCRs:-	
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#### 1. GENERAL

#### 1.1 SCOPE

This specification details the ratings, physical and electrical characteristics, test and inspection data for a silicon, monolithic, CMOS Dual J-K Master Slave Flip-Flop, having fully buffered outputs, based on Type 4027B. It shall be read in conjunction with ESA/SCC Generic Specification No. 9000, the requirements of which are supplemented herein.

#### 1.2 COMPONENT TYPE VARIANTS

Variants of the basic type integrated circuits specified herein, which are also covered by this specification, are given in Table 1(a).

#### 1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the integrated circuits specified herein, are as scheduled in Table 1(b).

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the applicable ESA/SCC Generic Specification.

#### 1.4 PARAMETER DERATING INFORMATION (FIGURE 1)

Not applicable.

#### 1.5 PHYSICAL DIMENSIONS

The physical dimensions of the integrated circuits specified herein are shown in Figure 2.

#### 1.6 PIN ASSIGNMENT

As per Figure 3(a).

#### 1.7 TRUTH TABLE

As per Figure 3(b).

#### 1.8 <u>CIRCUIT SCHEMATIC</u>

As per Figure 3(c).

#### 1.9 FUNCTIONAL DIAGRAM

As per Figure 3(d).

#### 1.10 HANDLING PRECAUTIONS

These devices are susceptible to damage by electrostatic discharge. Therefore, suitable precautions shall be employed for protection during all phases of manufacture, testing, packaging, shipment and any handling. These components are catagorised as Class 1 with a Minimum Critical Path Failure Voltage of 400Volts.

#### 1.11 INPUT PROTECTION NETWORK

Double diode protection shall be incorporated into each input as shown in Figure 3(e).



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# **TABLE 1(a) - TYPE VARIANTS**

VARIANT	CASE	FIGURE	LEAD MATERIAL AND/OR FINISH
01	FLAT	2(a)	G2 or G8
02	FLAT	2(a)	G4
03	D.I.L.	2(b)	. G2 or G8
04	D.I.L.	2(b)	G4
07	CHIP CARRIER	2(c)	2
08	D.I.L.	2(d)	G2
09	D.I.L.	2(d)	G4
10	SO CERAMIC	2(e)	G2
11	SO CERAMIC	2(e)	G4

#### **TABLE 1(b) - MAXIMUM RATINGS**

NO.	CHARACTERISTICS	SYMBOL	MAXIMUM RATINGS	UNITS	REMARKS
1	Supply Voltage	V <sub>DD</sub>	-0.5 to +18	V	Note 1
2	Input Voltage	V <sub>IN</sub>	-0.5 to V <sub>DD</sub> + 0.5	V	Note 2 Power on
3	D.C. Input Current	± I <sub>IN</sub>	10	mA	-
4	D.C. Output Current	± lo	10	mA	Note 3
5	Device Dissipation	P <sub>D</sub>	200	mWdc	Per Package
6	Output Dissipation	P <sub>DSO</sub>	100	mWdc	Note 4
7	Operating Temperature Range	T <sub>op</sub>	-55 to +125	°C	-
8	Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C	-
9	Soldering Temperature For FP and DIP For CCP	T <sub>sol</sub>	+300 +245	°C	Note 5 Note 6

#### **NOTES**

- 1. Device is functional from +3V to +15V with reference to V<sub>SS</sub>.
- 2.  $V_{DD}$  +0.5V should not exceed +18V.
- 3. The maximum output current of any single output.
- 4. The maximum power dissipation of any single output.
- 5. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.
- 6. Duration 30 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

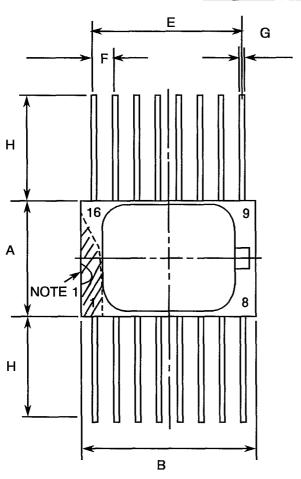


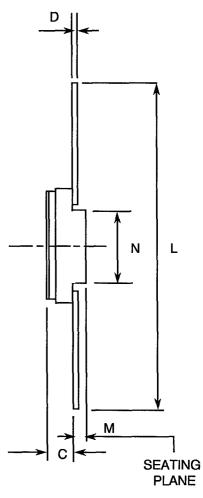
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# FIGURE 2 - PHYSICAL DIMENSIONS

# FIGURE 2(a) - FLAT PACKAGE, 16-PIN





SYMBOL	MILLIM	MILLIMETRES	
STIVIBUL	MIN	MAX	NOTES
Α	6.75	7.06	
В	9.76	10.14	
С	1.49	1.95	
D	0.102	0.152	3
E	8.76	9.01	
F	1.27	TYPICAL	4
G	0.38	0.48	3
Н	6.0	-	3
L	18.75	22.0	
М	0.33	0.43	
N	4.31	TYPICAL	



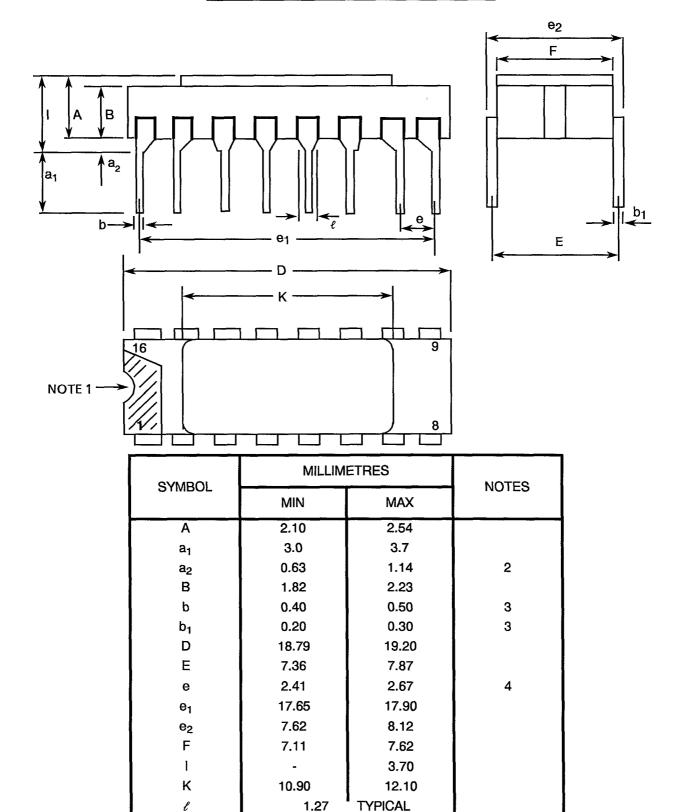
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#### FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

#### FIGURE 2(b) - DUAL-IN-LINE PACKAGE, 16-PIN



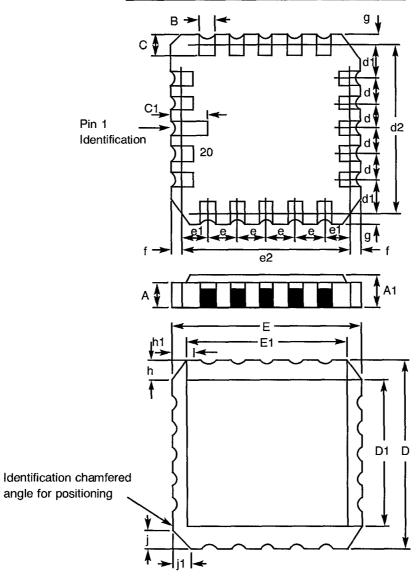
1.27

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# FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(c) - CHIP CARRIER - 20-TERMINAL



DIMENSIONS	MILLIM	MILLIMETRES	
DIVILIVOIONO	MIN	MAX	NOTES
A A1 B C C <sub>1</sub>	1.14 1.63 0.55 1.06 1.91	1.95 2.36 0.72 1.47 2.41	3 3
D D1 d, d1 d2 E	8.67 7.21 1.27 7.62 8.67	9.09 7.52 TYPICAL TYPICAL 9.09	4
E1 e, e1 e2	7.21 1.27 7.62	7.52 TYPICAL TYPICAL	4
f, g h, h1 j, j1	1.01 0.51	0.76 TYPICAL TYPICAL	6 5

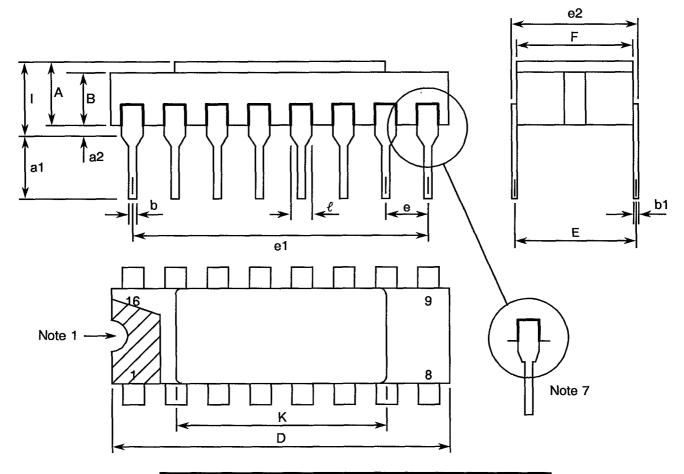


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# FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(d) - DUAL-IN-LINE PACKAGE, 16-PIN



SYMBOL	MILLIMETRES		NOTES
STIVIBUL	MIN	MAX	NOTES
Α	2.10	2.71	
a1	3.00	3.70	
a2	0.63	1.14	2
В	1.82	2.39	
b	0.40	0.50	3
b1	0.20	0.30	3
D	20.06	20.58	
E	7.36	7.87	
e	2.54 T	YPICAL	4
e1	17.65	17.90	
e2	7.62	8.12	
F	7.29	7.70	
1	-	3.83	
K	10.90	12.10	
l	1.14	1.50	

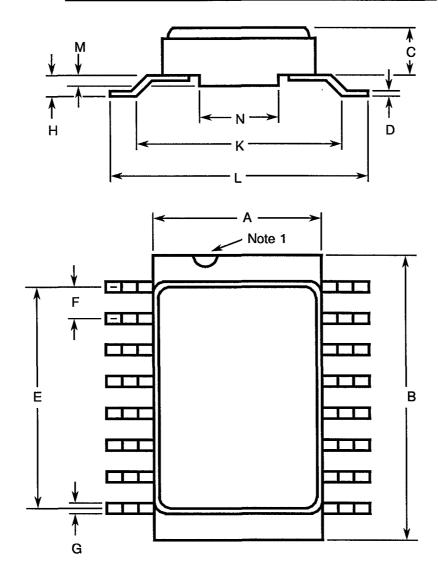


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# FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

# FIGURE 2(e) - SMALL OUTLINE CERAMIC PACKAGE, 16-PIN



SYMBOL	MILLIMETRES		NOTES
	MIN.	MAX.	NOTES
Α	6.75	7.06	
В	9.76	10.14	
С	1.49	1.95	
D	0.102	0.152	3
E	8.76	9.01	
F	1.27 TY	PICAL	4
G	0.38	0.48	3
Н	0.60	0.90	3
K	9.00 TYI	PICAL	
L	10	10.65	
M	0.33	0.43	
N	4.31 TYPICAL		



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#### FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

#### NOTES TO FIGURES 2(a) TO 2(e) INCLUSIVE

1. Index area: a notch, letter or dot shall be located adjacent to Pin 1 and shall be within the shaded area shown. For chip carrier packages the index shall be as defined in Figure 2(c).

- 2. The dimension shall be measured from the seating plane to the base plane.
- 3. All leads or terminals.

4. 16-pin packages

: 14 spaces.

20-terminal packages

: 12 spaces.

- 5. Index corner only.
- 6. Three non-index corners.
- 7. For all pins, either pin shape may be supplied.



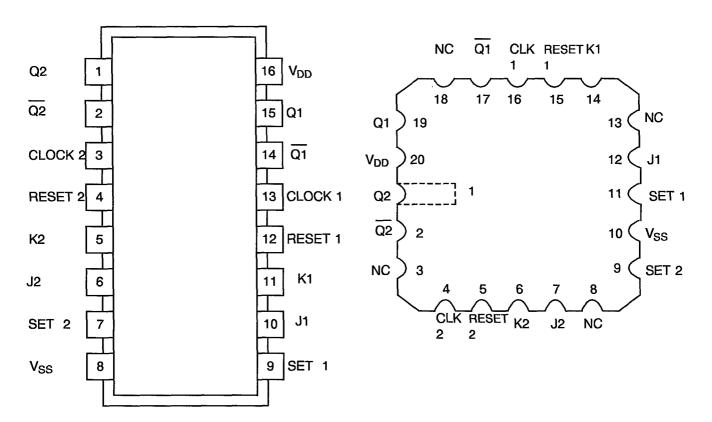
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#### FIGURE 3(a) - PIN ASSIGNMENT

#### DUAL-IN-LINE, SO AND FLAT PACKAGES

#### CHIP CARRIER PACKAGE



**TOP VIEW** 

**TOP VIEW** 

# FLAT PACKAGE, SO AND DUAL-IN-LINE TO CHIP CARRIER PIN ASSIGNMENT

FLAT PACKAGE, SO AND **DUAL-IN-LINE PIN OUTS** CHIP CARRIER PIN OUTS 1 

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# FIGURE 3(b) - TRUTH TABLE (EACH FLIP-FLOP)

	PR	ESEN'	T STA	TE		NEXT STATE		
	INPUTS		OUTPUT	CL	ОUТІ	PUTS		
J	K	S	R	Q	·	Q	Q	
Н	Х	L	L	L		Н	L	
×	L	L	L	Н	7	Н	L	
L	X	L	L	L	7	L	Н	
X	Н	L	L	Н		L	Н	
×	X	L	L	X	7_	NO CH	IANGE	
X	Χ	Н	L	х	×	Н	L	
×	X	L	Н	x	X	L	Н	
X	X	Н	Н	х	×	н	Н	

NOTES	1	Logic Levels Definitions: L	= Low Level	H = High	Level X=	Don't Car

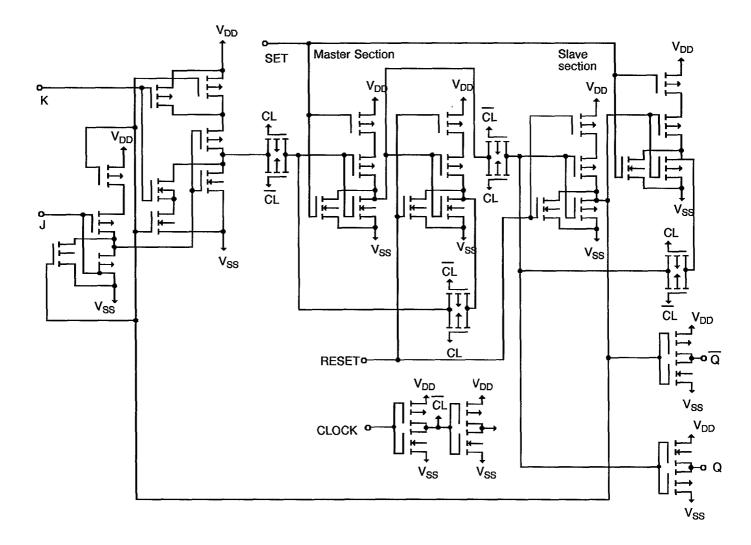
2. Positive-going Transition, Negative-going Transition,



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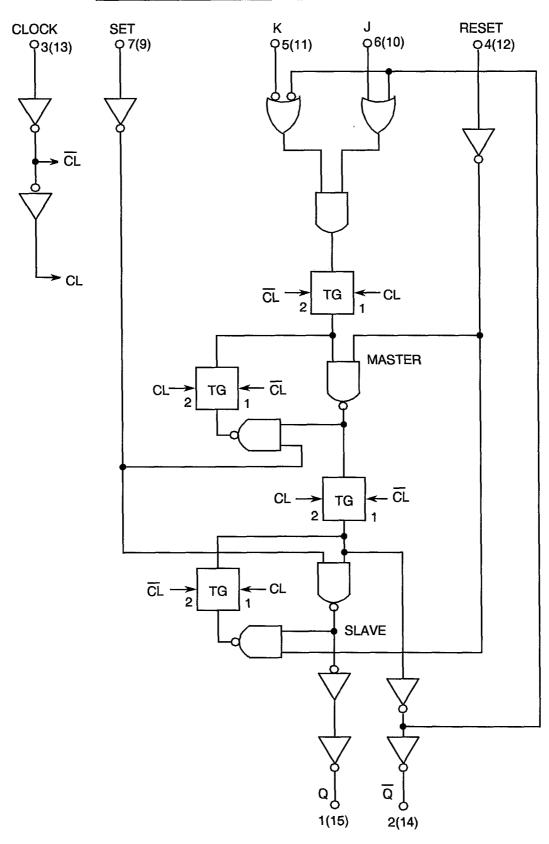
# FIGURE 3(c) - CIRCUIT SCHEMATIC (EACH FLIP-FLOP)



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# FIGURE 3(d) - FUNCTIONAL DIAGRAM (EACH FLIP-FLOP)

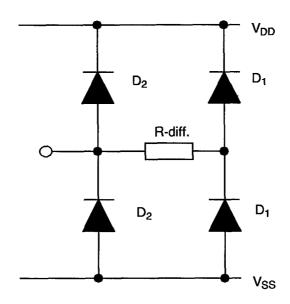




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# FIGURE 3(e) - INPUT PROTECTION NETWORK





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#### 2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:-

- (a) ESA/SCC Generic Specification No. 9000 for Integrated Circuits.
- (b) MIL-STD-883, Test Methods and Procedures for Micro-electronics.

#### 3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply. In addition, the following abbreviations are used:

V<sub>IC</sub> = Input Clamp Voltage

P<sub>DSO</sub> = Single Output Power Dissipation

CKT = Circuit.

#### 4. REQUIREMENTS

#### 4.1 GENERAL

The complete requirements for procurement of the integrated circuits specified herein are stated in this specification and ESA/SCC Generic Specification No. 9000 for Integrated Circuits. Deviations from the Generic Specification, applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

#### 4.2 <u>DEVIATIONS FROM GENERIC SPECIFICATION</u>

#### 4.2.1 Deviations from Special In-process Controls

None.

#### 4.2.2 Deviations from Final Production Tests (Chart II)

None.

#### 4.2.3 Deviations from Burn-in Tests (Chart III)

#### 4.2.3.1 Deviations from High Temperature Reverse Bias (H.T.R.B.)

Prior to operating power burn-in, a high temperature reverse bias (H.T.R.B.) screen at +125°C shall be added for the N-Channel and then for the P-Channel in accordance with Tables 5(a) and 5(b) of this specification. Each exposure to H.T.R.B. shall be 72 hours and Table 4 Parameter Drift Values shall be applied at 0 and 144 hours.

#### 4.2.4 Deviations from Qualification Tests (Chart IV)

None.



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#### 4.2.5 Deviations from Lot Acceptance Tests (Chart V)

None.

#### 4.3 MECHANICAL REQUIREMENTS

#### 4.3.1 Dimension Check

The dimensions of the integrated circuits specified herein shall be checked. They shall conform to those shown in Figure 2.

#### 4.3.2 Weight

The maximum weight of the integrated circuits specified herein shall be 1.5 grammes for the dual-in-line package, 0.6 grammes for the flat and SO packages and 0.52 grammes for the chip carrier package.

#### 4.4 MATERIALS AND FINISHES

The materials shall be as specified herein. Where a definite material is not specified, a material which will enable the integrated circuits specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

#### 4.4.1 Case

The case shall be hermetically sealed and have a metal body with hard glass seals or a ceramic body and the lids shall be welded, brazed or preform-soldered.

#### 4.4.2 <u>Lead Material and Finish</u>

For dual-in-line and flat packages, the material shall be Type 'G' with either Type '4' or Type '2 or 8' finish in accordance with ESA/SCC Basic Specification No. 23500. For chip carrier packages the finish shall be Type '2' in accordance with ESA/SCC Basic Specification No. 23500. For SO ceramic packages, the material shall be Type 'G' with either Type '2' or Type '4' finish in accordance with ESA/SCC Basic Specification No. 23500. (See Table 1(a) for Type Variants).

#### 4.5 MARKING

#### 4.5.1 General

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

#### 4.5.2 Lead Identification

For dual-in-line, flat and SO packages, an index shall be located at the top of the package in the position defined in Note 1 to Figure 2 or, alternatively, a tab may be used to identify Pin No. 1. The pin numbering must be read with the index or tab on the left-hand side. For chip carrier packages, the index shall be as defined by Figure 2(c).



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#### 4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:

	<u>920302201</u> B
Detail Specification Number	
Type Variant, as applicable	
Testing Level (B or C, as appropriate)	

#### 4.5.4 Traceability Information

Each component shall be marked in respect of traceability information in accordance with the requirements of ESA/SCC Basic Specification No. 21700.

#### 4.6 ELECTRICAL MEASUREMENTS

#### 4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured in respect of electrical characteristics are scheduled in Table 2. Unless otherwise specified, the measurements shall be performed at  $T_{amb} = +22 \pm 3$  °C.

#### 4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3. The measurements shall be performed at  $T_{amb} = +125 (+0-5)$  °C and -55(+5-0) °C respectively.

#### 4.6.3 <u>Circuits for Electrical Measurements</u>

Circuits and functional test sequence for use in performing electrical measurements listed in Tables 2 and 3 of this specification are shown in Figure 4.

#### 4.7 BURN-IN TESTS

#### 4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, measurements shall be performed at  $+22\pm3$  °C. The parameter drift values ( $\Delta$ ) applicable to the parameters scheduled, shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

#### 4.7.2 Conditions for H.T.R.B. and Burn-in

The requirements for H.T.R.B. and Burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 9000. The conditions for H.T.R.B. and Burn-in shall be as specified in Tables 5(a), 5(b) and 5(c) of this specification.

#### 4.7.3 Electrical Circuits for H.T.R.B and Burn-in

Circuits for use in performing the H.T.R.B. and Burn-in tests are shown in Figures 5(a), 5(b) and 5(c) of this specification.



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# TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS

NO	CUADACTEDICTION	CVMDOL	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIM	ITS	UNIT
NO.	CHARACTERISTICS	SYMBOL	MIL-STD 883	FIG.	D/F = DIP AND FP C = CCP)	MIN	MAX	UNIT
1	Functional Test	-	-	4(a)	Verify Truth Table without Load. V <sub>DD</sub> = 3Vdc, V <sub>SS</sub> = 0Vdc Notes 1 and 2	-	-	-
2	Functional Test	-	-	4(a)	Verify Truth Table without Load.  V <sub>DD</sub> = 15Vdc, V <sub>SS</sub> = 0Vdc Notes 1 and 2	-	1	-
3 to 6	Quiescent Current	I <sub>DD</sub>	3005	4(b)	$V_{IL}$ = 0Vdc, $V_{IH}$ = 15Vdc $V_{DD}$ = 15Vdc, $V_{SS}$ = 0Vdc Note 3 (Pin D/F 16) (Pin C 20)	-	500	nA
7 to 16	Input Current Low Level	I <sub>IL</sub>	3009	4(c)	$V_{IN}$ (Under Test) = 0Vdc All Other Inputs: $V_{IN}$ = 15Vdc $V_{DD}$ = 15Vdc, $V_{SS}$ = 0Vdc (Pins D/F 3-4-5-6-7-9-10- 11-12-13) (Pins C 4-5-6-7-9-11-12- 14-15-16)	-	-50	nA
17 to 26	Input Current High Level	ΙΗ	3010	4(d)	$V_{IN}$ (Under Test) = 15Vdc All Other Inputs: $V_{IN}$ = 0Vdc $V_{DD}$ = 15Vdc, $V_{SS}$ = 0Vdc (Pins D/F 3-4-5-6-7-9-10- 11-12-13) (Pins C 4-5-6-7-9-11-12- 14-15-16)	-	50	nA
27 to 28	Output Voltage Low Level at Q	V <sub>OL1</sub>	3007	4(e)	Flip-Flop (Under Test): $V_{IN}(SET) = 0Vdc$ $V_{IN}(RESET) = 15Vdc$ All Other Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = Open$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc, V_{SS} = 0Vdc$ (Pins D/F 1-15) (Pins C 1-19)	-	0.05	V



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# TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS (CONT'D)

NG.	OLIA DA OTEDIOTION	0)44501	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIM	ITS	LINUT
NO.	CHARACTERISTICS	SYMBOL	MIL-STD 883	FIG.	D/F = DIP AND FP C = CCP)	MIN	MAX	UNIT
29 to 30	Output Voltage Low Level at Q	V <sub>OL2</sub>	3007	4(e)	Flip-Flop (Under Test): $V_{IN}(SET) = 15Vdc$ $V_{IN}(RESET) = 0Vdc$ All Other Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = Open$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ (Pins D/F 2-14) (Pins C 2-17)	ı	0.05	V
31 to 34	Output Voltage High Level	V <sub>OH</sub>	3006	4(f)	Flip-Flop (Under Test): All Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = Open$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ (Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	14.95	•	V
35 to 36	Output Drive Current N-Channel at Q	I <sub>OL1</sub>	-	4(g)	Flip-Flop (Under Test): $V_{IN}(SET) = 0Vdc$ $V_{IN}(RESET) = 5Vdc$ All Other Inputs: $V_{IN} = 5Vdc$ $V_{OUT} = 0.4Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 5Vdc$ , $V_{SS} = 0Vdc$ Note 4 (Pins D/F 1-15) (Pins C 1-19)	0.51	-	mA
37 to 38	Output Drive Current N-Channel at Q	I <sub>OL2</sub>	-	4(g)	Flip-Flop (Under Test): $V_{IN}(SET) = 0Vdc$ $V_{IN}(RESET) = 15Vdc$ All Other Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = 1.5Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ Note 4 (Pins D/F 1-15) (Pins C 1-19)	3.4	-	mA



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# TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS (CONT'D)

No	OLIADAOTEDIOTICO	OVMPO!	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIM	ITS	LINUT
NO.	CHARACTERISTICS	SYMBOL	MIL-STD 883	FIG.	D/F = DIP AND FP C = CCP)	MIN	MAX	UNIT
39 to 40	Output Drive Current N-Channel at Q	l <sub>OL3</sub>	-	4(g)	Flip-Flop (Under Test): $V_{IN}(SET) = 5Vdc$ $V_{IN}(RESET) = 0Vdc$ All Other Inputs: $V_{IN} = 5Vdc$ $V_{OUT} = 0.4Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 5Vdc$ , $V_{SS} = 0Vdc$ Note 4 (Pins D/F 2-14) (Pins C 2-17)	0.51	-	mA
41 to 42	Output Drive Current N-Channel at Q	lol4	-	4(g)	Flip-Flop (Under Test): $V_{IN}(SET) = 15Vdc$ $V_{IN}(RESET) = 0Vdc$ All Other Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = 1.5Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ Note 4 (Pins D/F 2-14) (Pins C 2-17)	3.4	-	mA
43 to 46	Output Drive Current P-Channel	I <sub>OH1</sub>	-	4(h)	Flip-Flop (Under Test): All Inputs: $V_{IN} = 5Vdc$ $V_{OUT} = 4.6Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 5Vdc, V_{SS} = 0Vdc$ Note 4 (Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	-0.51	-	mA
47 to 50	Output Drive Current P-Channel	I <sub>OH2</sub>	-	4(h)	Flip-Flop (Under Test): All Inputs: $V_{IN} = 15 \text{Vdc}$ $V_{OUT} = 13.5 \text{Vdc}$ Other Flip-Flop: All Inputs: $V_{IN} = 0 \text{Vdc}$ $V_{DD} = 15 \text{Vdc}, V_{SS} = 0 \text{Vdc}$ Note 4 (Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	-3.4	-	mA
51	Input Voltage Low Level (Noise Immunity) (Functional Test)	V <sub>IL1</sub>	-	4(a)	V <sub>IL</sub> = 1.5Vdc V <sub>IH</sub> = 3.5Vdc V <sub>DD</sub> = 5 Vdc,V <sub>SS</sub> = 0Vdc Note 5	4.5	-	V
31	Input Voltage High Level (Noise Immunity) (Functional Test)	V <sub>IH1</sub>	-	+(a)	(Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	_	0.5	V

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# TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIM	ITS	UNIT
INO.	CHARACTERISTICS	STIVIBOL	MIL-STD 883	FIG.	D/F = DIP AND FP C = CCP)	MIN	MAX	CIVIT
52	Input Voltage Low Level (Noise Immunity) (Functional Test)	V <sub>IL2</sub>	-	4(a)	V <sub>IL</sub> = 4Vdc V <sub>IH</sub> = 11Vdc V <sub>DD</sub> = 15 Vdc,V <sub>SS</sub> = 0Vdc	13.5	-	V
J2	Input Voltage High Level (Noise Immunity) (Functional Test)	V <sub>IH2</sub>	-	-(α)	Note 5 (Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	•	1.5	
53	Threshold Voltage N-Channel	V <sub>THN</sub>	_	4(i)	Clock 2 Input at Ground All Other Inputs: V <sub>IN</sub> = 5Vdc V <sub>DD</sub> = 5Vdc, I <sub>SS</sub> =-10µA (Pin D/F 8) (Pin C 10)	-0.7	-3.0	V
54	Threshold Voltage P-Channel	V <sub>THP</sub>	-	4(j)	Clock 2 Input at Ground All Other Inputs: V <sub>IN</sub> = -5Vdc V <sub>SS</sub> = -5Vdc, I <sub>DD</sub> = 10µA (Pin D/F 16) (Pin C 20)	0.7	3.0	V
55 to 64	Input Clamp Voltage (to V <sub>SS</sub> )	V <sub>IC1</sub>	-	4(k)	$I_{\text{IN}}$ (Under Test) = -100 $\mu$ A $V_{\text{DD}}$ = Open, $V_{\text{SS}}$ = 0Vdc All Other Pins Open (Pins D/F 3-4-5-6-7-9-10-11-12-13) (Pins C 4-5-6-7-9-11-12-14-15-16)	-	-2.0	V
65 to 74	Input ClampVoltage (to V <sub>DD</sub> )	V <sub>IG2</sub>	-	4(I)	$V_{IN}$ (Under Test) = 6Vdc $V_{SS}$ = Open, R = 30k $\Omega$ ; (Pins D/F 3-4-5-6-7-9-10-11-12-13) (Pins C 4-5-6-7-9-11-12-14-15-16)	3.0	-	V



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# TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS

NO	OLIA DA OTEDIOTIOS	C)/MDOI	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIM	ITS	UNIT
NO.	CHARACTERISTICS	SYMBOL	MIL-STD 883	FIG.	D/F = DIP AND FP C = CCP)	MIN	MAX	UNIT
75 to 85	Input Capacitance	C <sub>IN</sub>	3012	4(m)	$V_{IN}$ (Not under Test) = 0Vdc $V_{DD} = V_{SS} = 0$ Vdc Note 6 (Pins D/F 3-4-5-6-7-9-10-11-12-13) (Pins C 4-5-6-7-9-11-12-14-15-16)	-	7.5	pF
86 to 87	Propagation Delay Low to High	ŧРLН	3003	4(n)	$V_{IN}$ (Under Test) = Pulse Generator $V_{DD}$ = 5Vdc, $V_{SS}$ = 0Vdc Note 7 Pins D/F Pins C 3 to 1 4 to 1 3 to 2 4 to 2	1	250	ns
88 to 89	Propagation Delay High to Low, Clock to Q or Q	t <sub>PHL</sub>	3003	4(n)	$\begin{array}{lll} V_{IN} \ (\text{Under Test}) &=& \text{Pulse} \\ \text{Generator} \\ V_{DD} &=& 5 \text{Vdc}, \ V_{SS} = 0 \text{Vdc} \\ \text{Note 7} \\ \hline \frac{\text{Pins D/F}}{3 \text{ to 1}} & \frac{\text{Pins C}}{4 \text{ to 1}} \\ \text{3 to 2} & \text{4 to 2} \\ \end{array}$	-	250	ns
90 to 91	Transition Time Low to High	tтLH	3004	4(n)	V <sub>IN</sub> (Under Test) = Pulse Generator V <sub>DD</sub> = 5Vdc, V <sub>SS</sub> = 0Vdc Note 7 (Pins D/F 1-2) (Pins C 1-2)	-	150	ns
92 to 93	Transition Time High to Low	t <sub>THL</sub>	3004	4(n)	V <sub>IN</sub> (Under Test) = Pulse Generator V <sub>DD</sub> = 5Vdc, V <sub>SS</sub> = 0Vdc Note 7 (Pins D/F 1-2) (Pins C 1-2)	-	150	ns
94	Maximum Clock Frequency	f <sub>(CL)</sub>	-	-	Flip-Flop under Test: Clock = Pulse Generator $V_{IN}$ (J and K) Inputs = 5Vdc All Other Inputs: $V_{IN}$ = 0Vdc Other Flip-Flop: All Inputs: $V_{IN}$ = 0Vdc $V_{DD}$ = 5Vdc, $V_{SS}$ = 0Vdc Notes 7 and 8 (Pin D/F 3) (Pin C 4)		-	MHz



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#### TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE (CONT'D)

#### **NOTES**

1. GO-NO-GO Test, each pattern of Test Table 4(a).

V<sub>OH</sub>≥V<sub>DD</sub> - 0.5Vdc V<sub>OL</sub>≤0.5Vdc

- 2. Maximum time to output comparator strobe 300µsec.
- 3. Test each pattern of Table 4(b).
- 4. Interchange of forcing and measuring function is permitted.
- 5. This is performed as a Functional Test in which extreme V<sub>IN</sub> conditions are applied and output voltage is measured.
- Measurement performed on a sample basis LTPD 7, or less, with a Capacitance Bridge connected between each input under test and V<sub>SS</sub>, only for Lots where LAT Level 2 is to be performed. (For LTPD sampling plan, see Annexe I of ESA/SCC 9000).
- 7. Measurement performed on a sample basis LTPD 7, or less (see Annexe I of ESA/SCC 9000).
- 8. A pulse, having the following conditions, shall be applied to the Clock Input:  $V_P = 0$ Vdc to  $V_{DD}$ Vdc. Maximum Clock Frequency  $f(C_L)$  requirement is considered met if proper output state changes occur with the pulse repetition rate set to that given in the "Limits" column.



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# TABLE 3(a) - ELECTRICAL MEASUREMENTS AT HIGH TEMPERATURE, +125(+0-5) °C

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIM	ITS	UNIT
NO.	OF IARACTERISTICS	STWIBOL	MIL-STD 883	FIG.	D/F = DIP AND FP C = CCP)	MIN	MAX	OIVIT
1	Functional Test	-	-	4(a)	Verify Truth Table without Load. V <sub>DD</sub> = 3Vdc, V <sub>SS</sub> = 0Vdc Notes 1 and 2	-	-	-
2	Functional Test	•	-	4(a)	Verify Truth Table without Load.  V <sub>DD</sub> = 15Vdc, V <sub>SS</sub> = 0Vdc Notes 1 and 2	•	•	-
3 to 6	Quiescent Current	I <sub>DD</sub>	3005	4(b)	$V_{IL}$ = 0Vdc, $V_{IH}$ = 15Vdc $V_{DD}$ = 15Vdc, $V_{SS}$ = 0Vdc Note 3 (Pin D/F 16) (Pin C 20)	1	15	μА
7 to 16	Input Current Low Level	կը_	3009	4(c)	$V_{IN}$ (Under Test) = 0Vdc All Other Inputs: $V_{IN}$ = 15Vdc $V_{DD}$ = 15Vdc, $V_{SS}$ = 0Vdc (Pins D/F 3-4-5-6-7-9-10- 11-12-13) (Pins C 4-5-6-7-9-11-12- 14-15-16)	-	-100	nA
17 to 26	Input Current High Level	l <sub>IH</sub>	3010	4(d)	$V_{IN}$ (Under Test) = 15Vdc All Other Inputs: $V_{IN}$ = 0Vdc $V_{DD}$ = 15Vdc, $V_{SS}$ = 0Vdc (Pins D/F 3-4-5-6-7-9-10- 11-12-13) (Pins C 4-5-6-7-9-11-12- 14-15-16)	-	100	nA
27 to 28	Output Voltage Low Level at Q	V <sub>OL1</sub>	3007	4(e)	Flip-Flop (Under Test): $V_{IN}(SET) = 0Vdc$ $V_{IN}(RESET) = 15Vdc$ All Other Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = Open$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ (Pins D/F 1-15) (Pins C 1-19)	-	0.05	V



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# TABLE 3(a) - ELECTRICAL MEASUREMENTS AT HIGH TEMPERATURE, + 125(+0-5) °C (CONT'D)

110	OLIADA OTEDIOTIO	OVANDO	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIM	ITS	LINUT
NO.	CHARACTERISTICS	SYMBOL	MIL-STD 883	FIG.	D/F = DIP AND FP C = CCP)	MIN	MAX	UNIT
29 to 30	Output Voltage Low Level at Q	V <sub>OL2</sub>	3007	4(e)	Flip-Flop (Under Test): $V_{IN}(SET) = 15Vdc$ $V_{IN}(RESET) = 0Vdc$ All Other Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = Open$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ (Pins D/F 2-14) (Pins C 2-17)	-	0.05	V
31 to 34	Output Voltage High Level	V <sub>OH</sub>	3006	4(f)	Flip-Flop (Under Test): All Inputs: $V_{IN} = 15 \text{Vdc}$ $V_{OUT} = \text{Open}$ Other Flip-Flop: All Inputs: $V_{IN} = 0 \text{Vdc}$ $V_{DD} = 15 \text{Vdc}$ , $V_{SS} = 0 \text{Vdc}$ (Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	14.95	-	>
35 to 36	Output Drive Current N-Channel at Q	I <sub>OL1</sub>	-	4(g)	Flip-Flop (Under Test): $V_{IN}(SET) = 0Vdc$ $V_{IN}(RESET) = 5Vdc$ All Other Inputs: $V_{IN} = 5Vdc$ $V_{OUT} = 0.4Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 5Vdc$ , $V_{SS} = 0Vdc$ Note 4 (Pins D/F 1-15) (Pins C 1-19)	0.36	-	mA
37 to 38	Output Drive Current N-Channel at Q	l <sub>OL2</sub>	-	4(g)	Flip-Flop (Under Test): $V_{IN}(SET) = 0Vdc$ $V_{IN}(RESET) = 15Vdc$ All Other Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = 1.5Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ Note 4 (Pins D/F 1-15) (Pins C 1-19)	2.4	-	mA



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# TABLE 3(a) - ELECTRICAL MEASUREMENTS AT HIGH TEMPERATURE, + 125(+0-5) °C (CONT'D)

	OLIADA OTEDIOTICO	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIM	ITS	UNIT
NO.	CHARACTERISTICS	SAMBOL	MIL-STD 883	FIG.	D/F = DIP AND FP C = CCP)	MIN	MAX	UNH
39 to 40	Output Drive Current N-Channel at Q	l <sub>OL3</sub>	-	4(g)	Flip-Flop (Under Test): $V_{IN}(SET) = 5Vdc$ $V_{IN}(RESET) = 0Vdc$ All Other Inputs: $V_{IN} = 5Vdc$ $V_{OUT} = 0.4Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 5Vdc$ , $V_{SS} = 0Vdc$ Note 4 (Pins D/F 2-14) (Pins C 2-17)	0.36	1	mA
41 to 42	Output Drive Current N-Channel at Q	I <sub>OL4</sub>	-	4(g)	Flip-Flop (Under Test): $V_{IN}(SET) = 15Vdc$ $V_{IN}(RESET) = 0Vdc$ All Other Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = 1.5Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ Note 4 (Pins D/F 2-14) (Pins C 2-17)	2.4	-	mA
43 to 46	Output Drive Current P-Channel	I <sub>OH1</sub>	<del>-</del>	4(h)	Flip-Flop (Under Test): All Inputs: $V_{IN} = 5Vdc$ $V_{OUT} = 4.6Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 5Vdc, V_{SS} = 0Vdc$ Note 4 (Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	-0.36	-	mA
47 to 50	Output Drive Current P-Channel	ІОН2	-	4(h)	Flip-Flop (Under Test): All Inputs: $V_{IN} = 15 \text{Vdc}$ $V_{OUT} = 13.5 \text{Vdc}$ Other Flip-Flop: All Inputs: $V_{IN} = 0 \text{Vdc}$ $V_{DD} = 15 \text{Vdc}, V_{SS} = 0 \text{Vdc}$ Note 4 (Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	-2.4	-	mA
51	Input Voltage Low Level (Noise Immunity) (Functional Test)	V <sub>IL1</sub>	-	4(a)	$V_{IL}$ = 1.5Vdc $V_{IH}$ = 3.5Vdc $V_{DD}$ = 5 Vdc, $V_{SS}$ = 0Vdc Note 5	4.5	-	V
51	Input Voltage High Level (Noise Immunity) (Functional Test)	V <sub>IH1</sub>	-	4(a)	(Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	-	0.5	V

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# TABLE 3(a) - ELECTRICAL MEASUREMENTS AT HIGH TEMPERATURE, + 125(+0-5) °C (CONT'D)

NO	NO. CHARACTERISTICS		TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIMITS		UNIT
NO.	CHARACTERISTICS	SYMBOL	MIL-STD 883	FIG.	D/F = DIP AND FP C = CCP)	MIN	MAX	ONIT
52	Input Voltage Low Level (Noise Immunity) (Functional Test)	V <sub>IL2</sub>	1	4(a)	V <sub>IL</sub> = 4Vdc V <sub>IH</sub> = 11Vdc V <sub>DD</sub> = 15 Vdc,V <sub>SS</sub> = 0Vdc	13.5	-	V
32	Input Voltage High Level (Noise Immunity) (Functional Test)	V <sub>IH2</sub>	-	-(α)	Note 5 (Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	-	1.5	
53	Threshold Voltage N-Channel	V <sub>THN</sub>	-	4(i)	Clock 2 Input at Ground All Other Inputs: V <sub>IN</sub> = 5Vdc V <sub>DD</sub> = 5Vdc, I <sub>SS</sub> =-10µA (Pin D/F 8) (Pin C 10)	-0.3	-3.5	٧
54	Threshold Voltage P-Channel	V <sub>THP</sub>	-	4(j)	Clock 2 Input at Ground All Other Inputs: V <sub>IN</sub> = -5Vdc V <sub>SS</sub> = -5Vdc, I <sub>DD</sub> = 10µA (Pin D/F 16) (Pin C 20)	0.3	3.5	V



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# TABLE 3(b) - ELECTRICAL MEASUREMENTS AT LOW TEMPERATURE, -55(+5-0) °C

luc l		0) (1) 47001	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIM	ITS	LINUT
NO.	CHARACTERISTICS	SYMBOL	MIL-STD 883	FIG.	D/F = DIP AND FP C = CCP)	MIN	MAX	UNIT
1	Functional Test	-	-	4(a)	Verify Truth Table without Load. V <sub>DD</sub> = 3Vdc, V <sub>SS</sub> = 0Vdc Notes 1 and 2	-	•	-
2	Functional Test	•	-	4(a)	Verify Truth Table without Load.  V <sub>DD</sub> = 15Vdc, V <sub>SS</sub> = 0Vdc Notes 1 and 2	-	1	-
3 to 6	Quiescent Current	I <sub>DD</sub>	3005	4(b)	$V_{IL}$ = 0Vdc, $V_{IH}$ = 15Vdc $V_{DD}$ = 15Vdc, $V_{SS}$ = 0Vdc Note 3 (Pin D/F 16) (Pin C 20)	•	500	nA
7 to 16	Input Current Low Level	I <sub>IL</sub>	3009	4(c)	$V_{IN}$ (Under Test) = 0Vdc All Other Inputs: $V_{IN}$ = 15Vdc $V_{DD}$ = 15Vdc, $V_{SS}$ = 0Vdc (Pins D/F 3-4-5-6-7-9-10- 11-12-13) (Pins C 4-5-6-7-9-11-12- 14-15-16)	-	-50	nA
17 to 26	Input Current High Level	ηн	3010	4(d)	$V_{IN}$ (Under Test) = 15Vdc All Other Inputs: $V_{IN}$ = 0Vdc $V_{DD}$ = 15Vdc, $V_{SS}$ = 0Vdc (Pins D/F 3-4-5-6-7-9-10- 11-12-13) (Pins C 4-5-6-7-9-11-12- 14-15-16)	-	50	nA
27 to 28	Output Voltage Low Level at Q	V <sub>OL1</sub>	3007	4(e)	Flip-Flop (Under Test): $V_{IN}(SET) = 0Vdc$ $V_{IN}(RESET) = 15Vdc$ All Other Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = Open$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ (Pins D/F 1-15) (Pins C 1-19)	-	0.05	V



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# TABLE 3(b) - ELECTRICAL MEASUREMENTS AT LOW TEMPERATURE, -55(+5-0) °C (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		LIAUT
						MIN	MAX	UNIT
29 to 30	Output Voltage Low Level at Q	V <sub>OL2</sub>	3007	4(e)	Flip-Flop (Under Test): $V_{IN}(SET) = 15Vdc$ $V_{IN}(RESET) = 0Vdc$ All Other Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = Open$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ (Pins D/F 2-14) (Pins C 2-17)	-	0.05	V
31 to 34	Output Voltage High Level	V <sub>ОН</sub>	3006	4(f)	Flip-Flop (Under Test): All Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = Open$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ (Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	14.95	ı	V
35 to 36	Output Drive Current N-Channel at Q	I <sub>OL1</sub>	-	4(g)	Flip-Flop (Under Test): $V_{IN}(SET) = 0Vdc$ $V_{IN}(RESET) = 5Vdc$ All Other Inputs: $V_{IN} = 5Vdc$ $V_{OUT} = 0.4Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 5Vdc$ , $V_{SS} = 0Vdc$ Note 4 (Pins D/F 1-15) (Pins C 1-19)	0.64	-	mA
37 to 38	Output Drive Current N-Channel at Q	l <sub>OL2</sub>	-	4(g)	Flip-Flop (Under Test): $V_{IN}(SET) = 0Vdc$ $V_{IN}(RESET) = 15Vdc$ All Other Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = 1.5Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ Note 4 (Pins D/F 1-15) (Pins C 1-19)	4.2	_	mA



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# TABLE 3(b) - ELECTRICAL MEASUREMENTS AT LOW TEMPERATURE, -55(+5-0) °C (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		LINUT
NO.						MIN	MAX	UNIT
29 to 30	Output Voltage Low Level at Q	V <sub>OL2</sub>	3007	4(e)	Flip-Flop (Under Test): $V_{IN}(SET) = 15Vdc$ $V_{IN}(RESET) = 0Vdc$ All Other Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = Open$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ (Pins D/F 2-14) (Pins C 2-17)	-	0.05	V
31 to 34	Output Voltage High Level	V <sub>ОН</sub>	3006	4(f)	Flip-Flop (Under Test): All Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = Open$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ (Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	14.95	•	٧
35 to 36	Output Drive Current N-Channel at Q	l <sub>OL1</sub>	-	4(g)	Flip-Flop (Under Test): $V_{IN}(SET) = 0Vdc$ $V_{IN}(RESET) = 5Vdc$ All Other Inputs: $V_{IN} = 5Vdc$ $V_{OUT} = 0.4Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 5Vdc$ , $V_{SS} = 0Vdc$ Note 4 (Pins D/F 1-15) (Pins C 1-19)	0.64	-	mA
37 to 38	Output Drive Current N-Channel at Q	l <sub>OL2</sub>	-	4(g)	Flip-Flop (Under Test): $V_{IN}(SET) = 0Vdc$ $V_{IN}(RESET) = 15Vdc$ All Other Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = 1.5Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ Note 4 (Pins D/F 1-15) (Pins C 1-19)	4.2	-	mA



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# TABLE 3(b) - ELECTRICAL MEASUREMENTS AT LOW TEMPERATURE, -55(+5-0) °C (CONT'D)

TABLE 3(b) - ELECTRICAL MEASUREMENTS AT LOW TEMPERATURE, -55(+5-0) C (CONT D)									
NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT	
						MIN	MAX		
39 to 40	Output Drive Current N-Channel at Q	l <sub>OL3</sub>	-	4(g)	Flip-Flop (Under Test): $V_{IN}(SET) = 5Vdc$ $V_{IN}(RESET) = 0Vdc$ All Other Inputs: $V_{IN} = 5Vdc$ $V_{OUT} = 0.4Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 5Vdc$ , $V_{SS} = 0Vdc$ Note 4 (Pins D/F 2-14) (Pins C 2-17)	0.64	·	mA	
41 to 42	Output Drive Current N-Channel at Q	l <sub>OL4</sub>	-	4(g)	Flip-Flop (Under Test): $V_{IN}(SET) = 15Vdc$ $V_{IN}(RESET) = 0Vdc$ All Other Inputs: $V_{IN} = 15Vdc$ $V_{OUT} = 1.5Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 15Vdc$ , $V_{SS} = 0Vdc$ Note 4 (Pins D/F 2-14) (Pins C 2-17)	4.2	-	mA	
43 to 46	Output Drive Current P-Channel	l <sub>OH1</sub>	-	4(h)	Flip-Flop (Under Test): All Inputs: $V_{IN} = 5Vdc$ $V_{OUT} = 4.6Vdc$ Other Flip-Flop: All Inputs: $V_{IN} = 0Vdc$ $V_{DD} = 5Vdc, V_{SS} = 0Vdc$ Note 4 (Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	-0.64		mA	
47 to 50	Output Drive Current P-Channel	I <sub>OH2</sub>	-	4(h)	Flip-Flop (Under Test): All Inputs: $V_{IN} = 15 \text{Vdc}$ $V_{OUT} = 13.5 \text{Vdc}$ Other Flip-Flop: All Inputs: $V_{IN} = 0 \text{Vdc}$ $V_{DD} = 15 \text{Vdc}, V_{SS} = 0 \text{Vdc}$ Note 4 (Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	-4.2	-	mA	
51	Input Voltage Low Level (Noise Immunity) (Functional Test)	V <sub>IL1</sub>	-	- 4(a)	- 4(a)	$V_{IL}$ = 1.5Vdc $V_{IH}$ = 3.5Vdc $V_{DD}$ = 5 Vdc, $V_{SS}$ = 0Vdc Note 5	4.5	-	V
51	Input Voltage High Level (Noise Immunity) (Functional Test)	V <sub>IH1</sub>	-			(Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	-	0.5	V

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## TABLE 3(b) - ELECTRICAL MEASUREMENTS AT LOW TEMPERATURE, -55(+5-0) °C (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIM	ITS	UNIT
NO.	CHARACTERISTICS	STIVIBOL	MIL-STD FIG. D/F = DIP AND FP C = CCP)		MIN	MAX	ONIT	
52	Input Voltage Low Level (Noise Immunity) (Functional Test)	V <sub>IL2</sub>	-	4(a)	V <sub>IL</sub> = 4Vdc V <sub>IH</sub> = 11Vdc V <sub>DD</sub> =15 Vdc,V <sub>SS</sub> =0Vdc	13.5	-	V
32	Input Voltage High Level (Noise Immunity) (Functional Test)	V <sub>IH2</sub>	-	+(α)	Note 5 (Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	-	1.5	v
53	Threshold Voltage N-Channel	V <sub>THN</sub>	-	4(i)	Clock 2 Input at Ground All Other Inputs: V <sub>IN</sub> = 5Vdc V <sub>DD</sub> = 5Vdc, I <sub>SS</sub> =-10µA (Pin D/F 8) (Pin C 10)	-0.7	-3.5	V
54	Threshold Voltage P-Channel	V <sub>THP</sub>	-	4(j)	Clock 2 Input at Ground All Other Inputs: V <sub>IN</sub> = -5Vdc V <sub>SS</sub> = -5Vdc, I <sub>DD</sub> = 10µA (Pin D/F 16) (Pin C 20)	0.7	3.5	V

NOTES: See Page 26.



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## FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

FIGURE 4(a) - FUNCTIONAL TEST TABLE

PATTERN		PIN NUMBERS D.C. SUPPLY														
NO.	1	2	3	4	5	6	7	9	10	11	12	13	14	15	8	16
1	0	1	1	1	0	0	0	0	0	0	1	1	1	0	0	$V_{\mathrm{DD}}$
2	0	1	1	0	0	0	0	0	0	0	0	1	1	0	1	
3	1	0	1	0	1	0	1	0	0	0	0	1	1	0		
4	1	0	1	0	1	0	0	0	0	0	0	1	1	0		
5	0	1	1	1	0	1	0	0	0	0	0	1	1	0		
6	1	1	1	1	0	1	1	0	0	0	0	1	1	0		
7	1	1	1	1	0	1	1	0	0	0	0	1	1	0		
8	1	0	0	0	1	1	1	0	0	0	0	1	1	0		
9	1	0	0	0	1	1	0	0	0	0	0	1	1	0		
10	0	1	0	1	0	0	0	0	0	0	0	1	1	0		
11	0	1	1	0	0	0	0	0	0	0	0	1	1	0		
12	0	1	1	0	0	0	0	1	0	1	0	1	0	1		
13	0	1	1	0	0	1	0	0	0	1	0	1	0	1		
14	0	1	0	0	0	1	0	0	1	0	1	1	1	0		
15	0	1	0	0	0	0	0	1	1	0	1	1	1	1		
16	0	1	1	0	0	0	0	1	1	0	1	0	1	1		
17	0	1	0	0	0	0	0	1	1	1	0	0	0	1		
18	0	1	0	0	0	1	0	0	1	1	0	0	0	1		
19	1	0	1	0	0	1	0	0	0	0	1	0	1	0		
20	1	0	0	0	1	0	0	0	0	0	0	0	1	0		
21	0	1	1	0	1	0	0	0	0	0	0	0	1	0		
22	0	1	0	0	1	1	0	0	0	0	0	0	1	0		
23	1	0	1	0	1	1	0	0	0	0	0	0	1	0		
24	1	0	0	0	0	1	0	0	0	0	0	0	1	0		
25	1	0	1	0	0	1	0	0	0	0	0	0	1	0		
26	1	0	0	0	1	1	0	0	0	0	0	0	1	0	1	
27	0	1	1	0	1	1	0	0	0	0	0	0	1	0		
28	0	1	0	0	1	0	0	0	0	0	0	0	1	0		
29	0	1	1	0	1	0	0	0	0	0	0	0	1	0		
30	0	1	0	0	0	0	0	0	0	0	0	0	1	0		
31	0	1	0	0	0	0	0	0	0	0	0	1	1	0		
32	0	1	0	0	0	0	0	0	1	0	0	1	1	0		
33	0	1	0	0	0	0	0	0	1	0	0	0	1	0		
34	0	1	0	0	0	0	0	0	0	0	0	0	1	0	*	<b>\</b>

NOTES: See Page 36.



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#### FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

#### FIGURE 4(a) - FUNCTIONAL TEST TABLE (CONTINUED)

PATTERN						PIN	NUI	MBE	RS						D.C.	SUPPLY
NO.	1	2	3	4	5	6	7	9_	10	11	12	13	14	15	8	16_
35	0	1	0	0	0	0	0	0	0	0	0	1	1	0	0	$V_{\mathrm{DD}}$
36	0	1	0	0	0	0	0	0	0	0	0	0	1	0		
37	0	1	0	0	0	0	0	0	1	0	0	0	1	0		
38	0	1	0	0	0	0	0	0	1	0	0	1	0	1		
39	0	1	0	0	0	0	0	0	0	1	0	0	0	1		
40	0	1	0	0	0	0	0	0	0	1	0	1	1	0	1	1
41	0	1	0	0	0	0	0	0	1	1	0	0	1	0		
42	0	1	0	0	0	0	0	0	1	1	0	1	0	1		
43	0	1	0	0	0	0	0	0	1	0	0	0	0	1		
44	0	1	0	0	0	0	0	0	1	0	0	1	0	1	1	
45	0	1	0	0	0	0	0	0	1	1	0	0	0	1		
46	0	1	0	0	0	0	0	0	1	1	0	1	1	0		
47	0	1	0	0	0	0	0	0	0	1	0	0	1	0		
48	0	1	0	0	0	0	0	0	0	1	0	1	1	0		
49	0	1	0	0	0	0	0	0	0	1	0	0	1	0	1	
50	1	0	1	0	1	1	1	1	1	1	0	1	0	1		
51	0	1	0	1	0	0	0	0	0	0	1	0	_ 1	0	<b>Y</b>	Ψ

#### **NOTES**

- 1. Figure 4(a) illustrates one series of test patterns. Any other pattern series must be agreed with the Qualifying Space Agency and shall be included as an Appendix.
- 2. Logic Level Definitions:  $1 = V_{IH} = V_{DD}$ ,  $0 = V_{IL} = V_{SS}$ .

#### FIGURE 4(b) - QUIESCENT CURRENT TEST TABLE

		PIN NUMBERS								D.C. 8	SUPPLY					
PATTERN NO.		INPUTS OUTPUTS						3	7							
110.	3	13	4	12	6	10	5	11	7	9	1	15	2	14	8	16
1	1	1	1	1	1	1	0	0	0	0	Х	Χ	Х	Х	V <sub>SS</sub>	$V_{DD}$
2	1	1	0	0	0	0	1	1	0	0	Х	Χ	Χ	Χ		
3	0	0	1	1	0	0	0	0	1	1	Х	Χ	Χ	Х		
4	0	0	0	0	1	1	1	1	1	1	Х	X	Χ	Χ		<b>V</b>

#### <u>NOTES</u>

- 1. Figure 4(b) illustrates one series of test patterns. Any other pattern series must be agreed with the Qualifying Space Agency and shall be included as an Appendix.
- 2. Logic Level Definitions:  $1 = V_{IH} = V_{DD}$ ,  $0 = V_{IL} = V_{SS}$ , X = Don't Care.



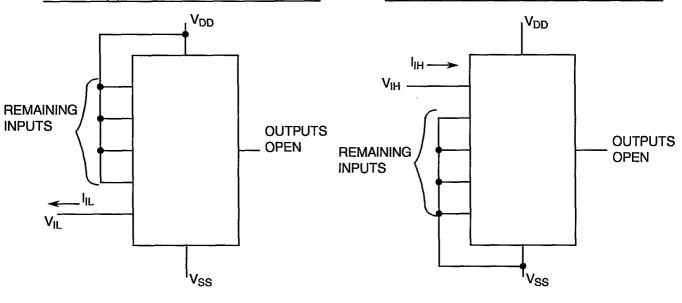
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#### FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

#### FIGURE 4(c) - LOW LEVEL INPUT CURRENT

#### FIGURE 4(d) - HIGH LEVEL INPUT CURRENT



#### **NOTES**

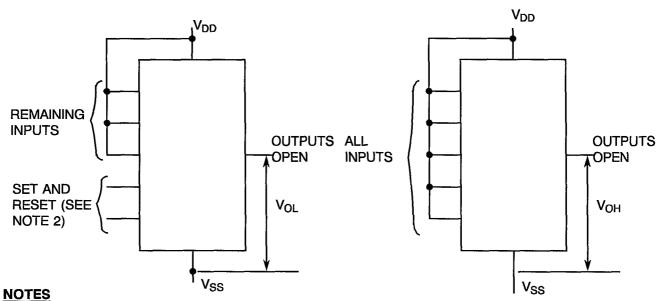
1. Each input to be tested separately.

#### **NOTES**

1. Each input to be tested separately.

#### FIGURE 4(e) - LOW LEVEL OUTPUT VOLTAGE

#### FIGURE 4(f) - HIGH LEVEL OUTPUT VOLTAGE



- 1. Each output to be tested separately.
- 2. For  $V_{OL1}$ : SET = 0Vdc

RESET = 15Vdc

For  $V_{OL2}$ : SET = 15Vdc

RESET = 0Vdc

#### **NOTES**

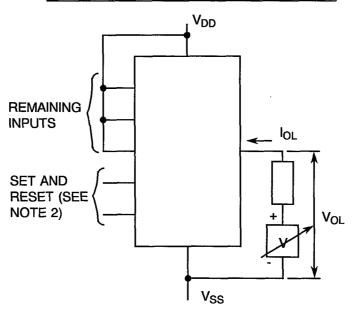
1. Each output to be tested separately.

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#### FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

#### FIGURE 4(g) - LOW LEVEL OUTPUT CURRENT



#### **NOTES**

1. Each output to be tested separately.

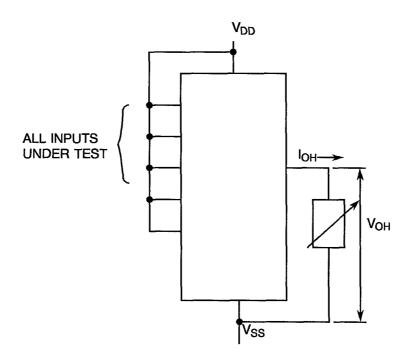
2. For Q: SET = 0Vdc

RESET = 5 or 15Vdc

For  $\overline{Q}$ : SET = 5 or 15Vdc

RESET = 0Vdc

#### FIGURE 4(h) - HIGH LEVEL OUTPUT CURRENT



#### **NOTES**

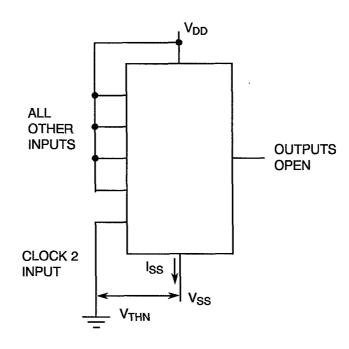
1. Each output to be tested separately.

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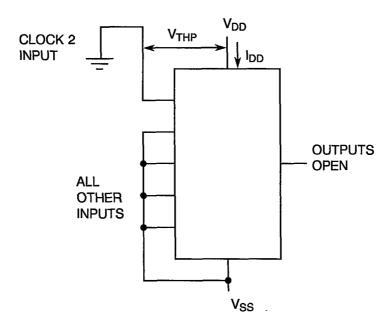
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### FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

### FIGURE 4(i) - THRESHOLD VOLTAGE N-CHANNEL



#### FIGURE 4(j) - THRESHOLD VOLTAGE P-CHANNEL



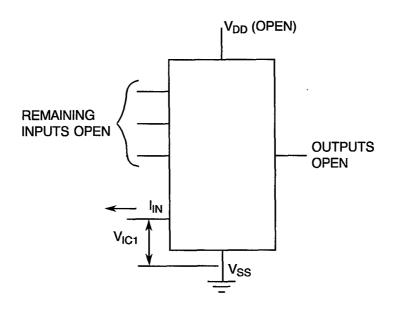


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### FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

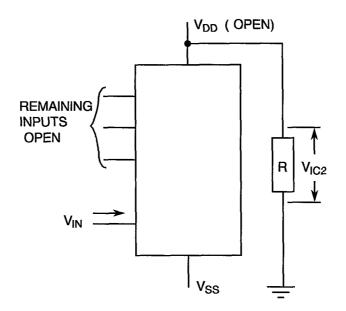
FIGURE 4(k) - INPUT CLAMP VOLTAGE (VSS)



#### **NOTES**

1. All inputs to be tested separately.

### FIGURE 4(I) - INPUT CLAMP VOLTAGE (VDD)



#### **NOTES**

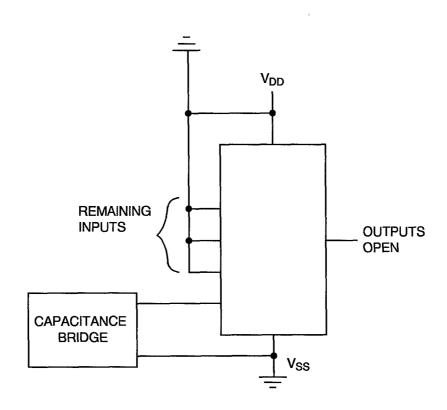
1. All inputs to be tested separately.

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### FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(m) - INPUT CAPACITANCE



#### **NOTES**

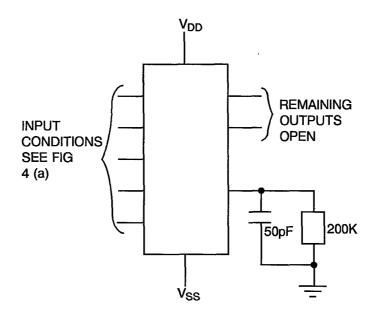
- 1. Each input to be tested separately.
- 2. f = 100kHz to 1MHz

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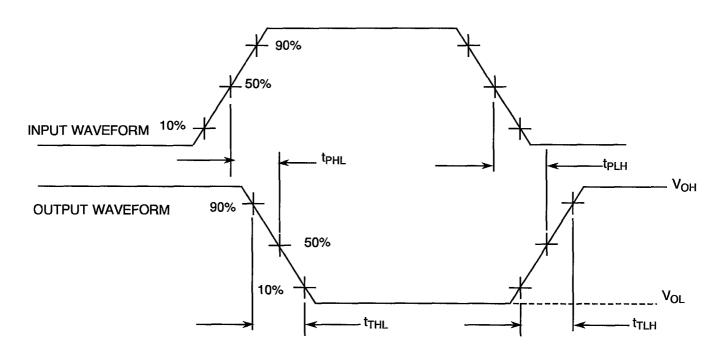
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#### FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

#### FIGURE 4(n) - PROPAGATION DELAY AND TRANSITION TIME



#### **VOLTAGE WAVEFORMS**



**NOTES** 1. Pulse Generator -  $V_P$  = 0 to  $V_{DD}$  ,  $t_r$  and  $t_f \le 15 \text{ns}$ , f = 500 kHz.



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## TABLE 4 - PARAMETER DRIFT VALUES

NO.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
3 to 6	Quiescent Current	I <sub>DD</sub>	As per Table 2	As per Table 2	± 75	nA
35 to 36	Output Drive Current N-Channel at Q	l <sub>OL1</sub>	As per Table 2	As per Table 2	±15 (1)	%
39 to 40	Output Drive Current N-Channel at Q	l <sub>OL3</sub>	As per Table 2	As per Table 2	±15 (1)	%
43 to 46	Output Drive Current P-Channel	I <sub>OH1</sub>	As per Table 2	As per Table 2	±15 (1)	%
53	Threshold Voltage N-Channel	$V_{THN}$	As per Table 2	As per Table 2	± 0.3	V
54	Threshold Voltage P-Channel	V <sub>THP</sub>	As per Table 2	As per Table 2	±0.3	V

**NOTES** 1. Percentage of limit value if voltage is the measurement function.



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## TABLE 5(a) - CONDITIONS FOR BURN-IN HIGH TEMPERATURE REVERSE BIAS, N-CHANNEL

NO.		CHARACTERISTICS	SYMBOL	CONDITION	UNIT
1	Ambient T	emperature	T <sub>amb</sub>	+ 125( + 0-5)	°C
2	Outputs -	(Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	V <sub>OUT</sub>	Open	
3	Inputs -	(Pins D/F 7-9) (Pins C 9-11)	V <sub>IN</sub>	Ground	Vdc
4	Inputs -	(Pins D/F 3-4-5-6-10-11-12-13) (Pins C 4-5-6-7-12-14-15-16)	V <sub>IN</sub>	15	Vdc
5	Positive S (Pin D/F 1 (Pin C 20)	•	V <sub>DD</sub>	15	Vdc
6	Negative 3 (Pin D/F 8 (Pin C 10)	•	V <sub>SS</sub>	Ground	Vdc

**NOTES** 1. Input Load = Protection Resistor =  $2k\Omega$  minimum to  $47k\Omega$  maximum.

#### TABLE 5(b) - CONDITIONS FOR BURN-IN HIGH TEMPERATURE REVERSE BIAS, P-CHANNEL

NO.		CHARACTERISTICS	SYMBOL	CONDITION	UNIT
1	Ambient T	emperature	T <sub>amb</sub>	+ 125( + 0-5)	°C
2	Outputs -	(Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	V <sub>OUT</sub>	Open	-
3	Inputs -	(Pins D/F 3-4-5-6-10-11-12-13) (Pins C 4-5-6-7-12-14-15-16)	V <sub>IN</sub>	Ground	Vdc
4	Inputs -	(Pins D/F 7-9) (Pins C 9-11)	V <sub>IN</sub>	15	Vdc
5	Positive S (Pin D/F 1 (Pin C 20)		V <sub>DD</sub>	15	Vdc
6	Negative 5 (Pin D/F 8 (Pin C 10)		V <sub>SS</sub>	Ground	Vdc

**NOTES** 1. Input Load = Protection Resistor =  $2k\Omega$  minimum to  $47k\Omega$  maximum.



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## TABLE 5(c) - CONDITIONS FOR BURN-IN DYNAMIC

NO.	CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT
1	Ambient Temperature	T <sub>amb</sub>	+ 125( + 0-5)	°C
2	Outputs - (Pins D/F 1-2-14-15) (Pins C 1-2-17-19)	V <sub>OUT</sub>	V <sub>DD/2</sub>	Vdc
3	Inputs - (Pins D/F 5-6-10-11) (Pins C 6-7-12-14)	V <sub>IN</sub>	$V_{DD}$	Vdc
4	Inputs - (Pins D/F 4-7-9-12) (Pins C 5-9-11-15)	ViN	Ground	Vdc
5	Inputs - (Pins D/F 3-13) (Pins C 4-16)	V <sub>IN</sub>	V <sub>GEN</sub>	Vac
6	Pulse Voltage	V <sub>GEN</sub>	0V to V <sub>DD</sub>	Vac
7	Pulse Frequency Square Wave	f	50k≤f<1M 50% Duty Cycle	Hz
8	Positive Supply Voltage (Pin D/F 16) (Pin C 20)	V <sub>DD</sub>	15	Vdc
9	Negative Supply Voltage (Pin D/F 8) (Pin C 10)	V <sub>SS</sub>	Ground	Vdc

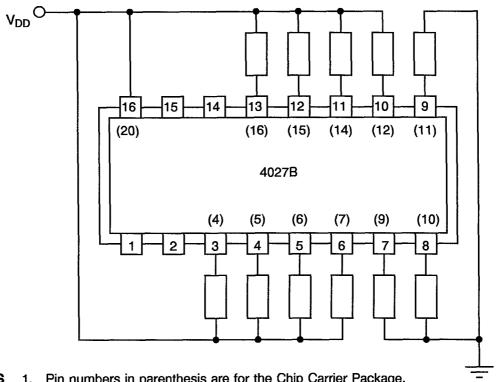
**NOTES** 1. Input Load = Output Load =  $2k\Omega$  minimum to  $47k\Omega$  maximum.



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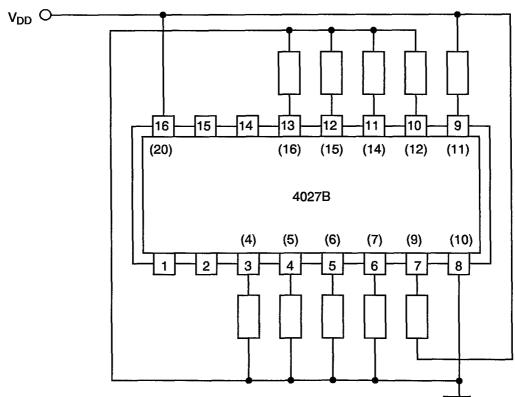
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## FIGURE 5(a) - ELECTRICAL CIRCUIT FOR BURN-IN HIGH TEMPERATURE REVERSE BIAS, N-CHANNELS



**NOTES** 1. Pin numbers in parenthesis are for the Chip Carrier Package.

#### FIGURE 5(b) - ELECTRICAL CIRCUIT FOR BURN-IN HIGH TEMPERATURE REVERSE BIAS, P-CHANNELS

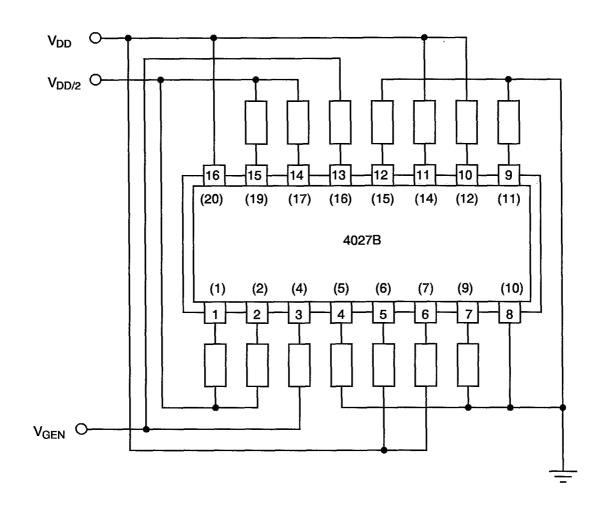


**NOTES** 1. Pin numbers in parenthesis are for the Chip Carrier Package.

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### FIGURE 5(c) - ELECTRICAL CIRCUIT FOR BURN-IN DYNAMIC



**NOTES** 1. Pin numbers in parenthesis are for the Chip Carrier Package.



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## 4.8 <u>ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC</u> SPECIFICATION NO. 9000)

#### 4.8.1 Electrical Measurements on Completion of Environmental Tests

The parameters to be measured on completion of environmental tests are scheduled in Table 6. Unless otherwise stated, the measurements shall be performed at  $T_{amb} = +22\pm3$  °C.

#### 4.8.2 Electrical Measurements at Intermediate Points during Endurance Tests

The parameters to be measured at intermediate points during endurance tests are as scheduled in Table 6 of this specification.

#### 4.8.3 <u>Electrical Measurements on Completion of Endurance Tests</u>

The parameters to be measured on completion of endurance testing are as scheduled in Table 6 of this specification. Unless otherwise stated, the measurements shall be performed at  $T_{amb} = +22 \pm 3$  °C.

#### 4.8.4 Conditions for Operating Life Test

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 9000. The conditions for operating life testing shall be as specified in Table 5(c) of this specification.

#### 4.8.5 <u>Electrical Circuits for Operating Life Tests</u>

Circuits for use in performing the operating life tests are shown in Figure 5(c) of this specification.

#### 4.8.6 <u>Conditions for High Temperature Storage Test</u>

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 9000. The temperature to be applied shall be the maximum storage temperature specified in Table 1(b) of this specification.



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## TABLE 6 - ELECTRICAL MEASUREMENTS ON COMPLETION OF ENVIRONMENTAL TESTS AND AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING

				III CETTOR OF BRIDE				
NO	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS			UNIT
			TEST METHOD		(Δ)	MIN	MAX	
1	Functional Test	-	As per Table 2	As per Table 2	-	-	-	-
3 to 6	Quiescent Current	I <sub>DD</sub>	As per Table 2	As per Table 2	± 75	-	-	nA
7 to 16	Input Current Low Level		As per Table 2	As per Table 2	•	-	-50	nA
17 to 26	Input Current High Level	lіН	As per Table 2	As per Table 2	-	-	50	nA
27 to 28	Output Voltage Low Level at Q	V <sub>OL1</sub>	As per Table 2	As per Table 2	-	-	0.05	V
29 to 30	Output Voltage Low Level at Q	V <sub>OL2</sub>	As per Table 2	As per Table 2	-	-	0.05	V
31 to 34	Output Voltage High Level	V <sub>OH</sub>	As per Table 2	As per Table 2	-	14.95	-	V
35 to 36	Output Drive Current N-Channel at Q	l <sub>OL1</sub>	As per Table 2	As per Table 2	± 15 (1)	-	-	%
37 to 38	Output Drive Current N-Channel at Q	l <sub>OL2</sub>	As per Table 2	As per Table 2	± 15 (1)	-	-	%
39 to 40	Output Drive Current N-Channel at Q	I <sub>OL3</sub>	As per Table 2	As per Table 2	± 15 (1)	-	-	%
41 to 42	Output Drive Current N-Channel at Q	I <sub>OL4</sub>	As per Table 2	As per Table 2	± 15 (1)	-	_	%
43 to 46	Output Drive Current P-Channel	I <sub>OH1</sub>	As per Table 2	As per Table 2	± 15 (1)	-	-	%



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# TABLE 6 - ELECTRICAL MEASUREMENTS ON COMPLETION OF ENVIRONMENTAL TESTS AND AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING

					CHANGE			
NO	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	LIMITS (Δ)	MIN	MAX	UNIT
1	Functional Test	-	As per Table 2	As per Table 2	-	-	-	-
3 to 6	Quiescent Current	I <sub>DD</sub>	As per Table 2	As per Table 2	± 75	-	ı	nA
7 to 16	Input Current Low Level	I <sub>E</sub> L	As per Table 2	As per Table 2	-	-	-50	nA
17 to 26	Input Current High Level	JIН	As per Table 2	As per Table 2	-	1	50	nA
27 to 28	Output Voltage Low Level at Q	V <sub>OL1</sub>	As per Table 2	As per Table 2	-	1	0.05	٧
29 to 30	Output Voltage Low Level at Q	V <sub>OL2</sub>	As per Table 2	As per Table 2	-	-	0.05	V
31 to 34	Output Voltage High Level	V <sub>OH</sub>	As per Table 2	As per Table 2	-	14.95		V
35 to 36	Output Drive Current N-Channel at Q	I <sub>OL1</sub>	As per Table 2	As per Table 2	± 15 (1)	-	-	%
37 to 38	Output Drive Current N-Channel at Q	l <sub>OL2</sub>	As per Table 2	As per Table 2	± 15 (1)	-	,	%
39 to 40	Output Drive Current N-Channel at Q	I <sub>OL3</sub>	As per Table 2	As per Table 2	± 15 (1)	-	-	%
41 to 42	Output Drive Current N-Channel at Q	I <sub>OL4</sub>	As per Table 2	As per Table 2	± 15 (1)	-	-	%
43 to 46	Output Drive Current P-Channel	I <sub>OH1</sub>	As per Table 2	As per Table 2	± 15 (1)	-	-	%

**NOTES** 1. Percentage of limit value if voltage is the measurement function.



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## TABLE 6 - ELECTRICAL MEASUREMENTS ON COMPLETION OF ENVIRONMENTAL TESTS AND AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING (CONT'D)

NO	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST	TEST	CHANGE LIMITS			UNIT
INO	CHARACTERISTICS	STIVIDOL	METHOD	CONDITIONS	(Δ)	MIN	MAX	ONIT
47 to 50	Output Drive Current P-Channel	I <sub>OH2</sub>	As per Table 2	As per Table 2	± 15 (1)	1	1	%
51	Input Voltage Low Level (Noise Immunity) (Functional Test)	V <sub>IL1</sub>	As an Table O	As you Table O	<del>-</del>	4.5	1	
	Input Voltage High Level (Noise Immunity) (Functional Test)	V <sub>IH1</sub>	As per Table 2	As per Table 2	-	-	0.5	V
53	Threshold Voltage N-Channel	V <sub>THN</sub>	As per Table 2	As per Table 2	± 0.3		-	V
54	Threshold Voltage P-Channel	$V_{THP}$	As per Table 2	As per Table 2	± 0.3	•	•	V

NOTES 1. Percentage of limit value if voltage is the measurement function.



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## **APPENDIX 'A'**

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### AGREED DEVIATIONS FOR STMICROELECTRONICS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATION
Para. 4.2.3	Para. 9.23, High Temperature Reverse Bias Burn-in: The temperature limits of MIL-STD-883, Para. 4.5.8(c) may be used.  Para. 9.24, Power Burn-in: The temperature limits of MIL-STD-883, Para. 4.5.8(c) may be used.
Para. 4.2.4	Para. 9.21.1, Operating Life during Qualification Testing: The temperature limits of MIL-STD-883, Para. 4.5.8(c) may be used.
Para. 4.2.5	Para. 9.21.2, Operating Life during Lot Acceptance Testing: The temperature limits of MIL-STD-883, Para. 4.5.8(c) may be used.